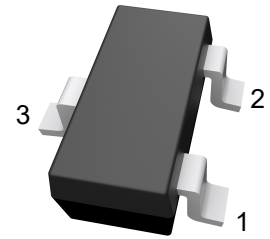




PJM3400NSC

N- Enhancement Mode Field Effect Transistor

SOT-23-3



1. Gate 2. Source 3. Drain
Marking: P0

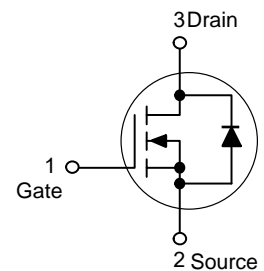
Features

- $V_{DS} = 30V, I_D = 5.8A$
 $R_{DS(ON)} < 45m\Omega @ V_{GS}=2.5V$
 $R_{DS(ON)} < 31m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 27m\Omega @ V_{GS}=10V$
- High power and current handling capability

Applications

- Load switch and in PWM applications
- Power management

Schematic diagram



Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	5.8	A
Drain Current-Pulsed ^{Note1}	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	89	°C/W
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Electrical Characteristics

(T_A=25°C unless otherwise noted)

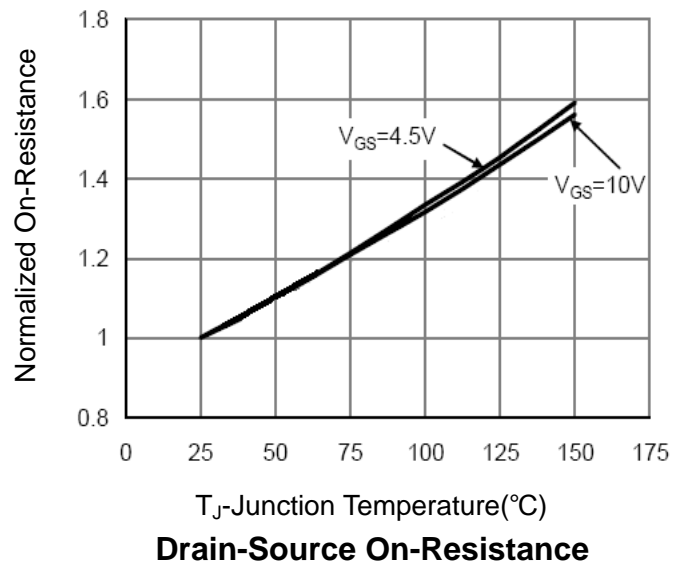
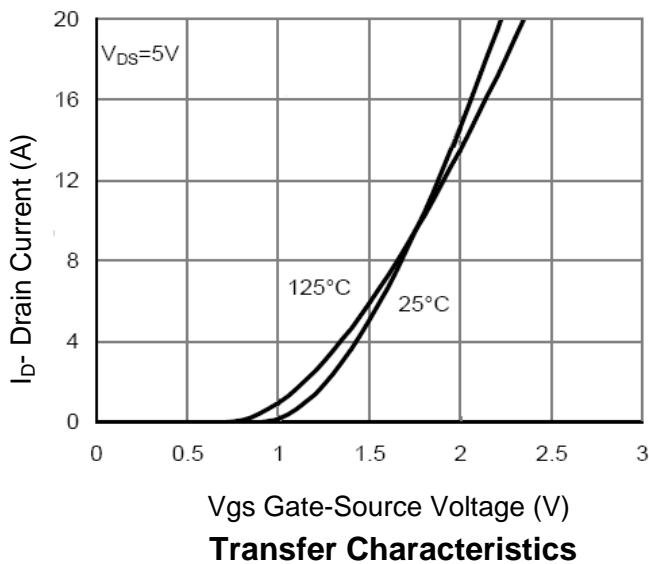
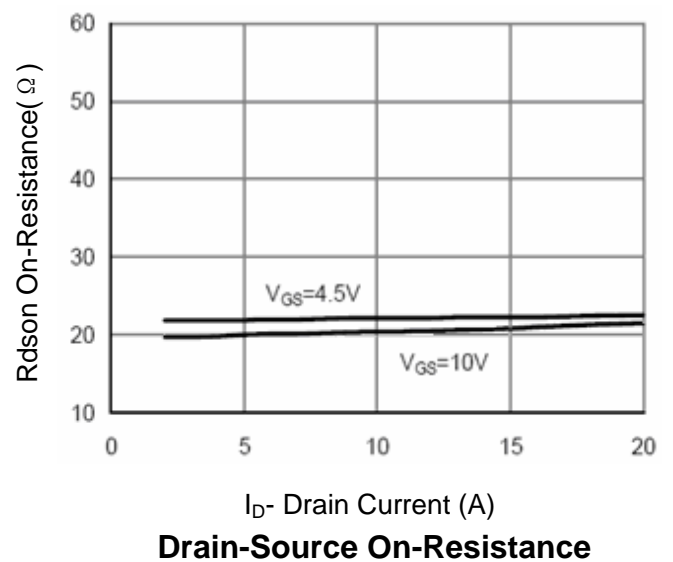
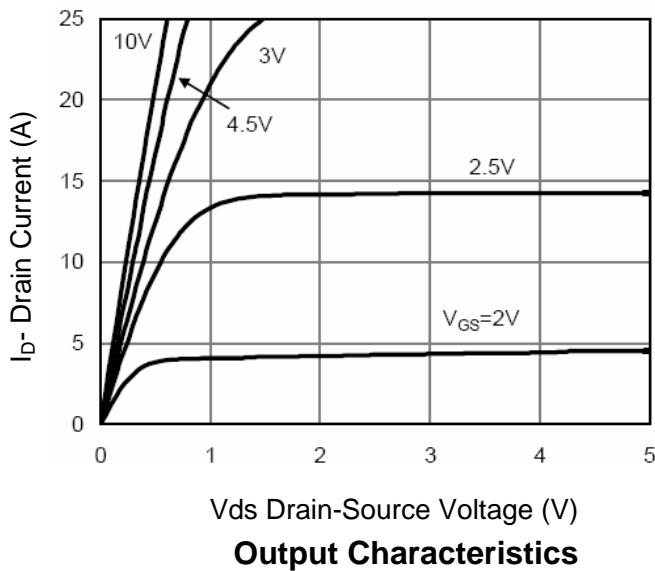
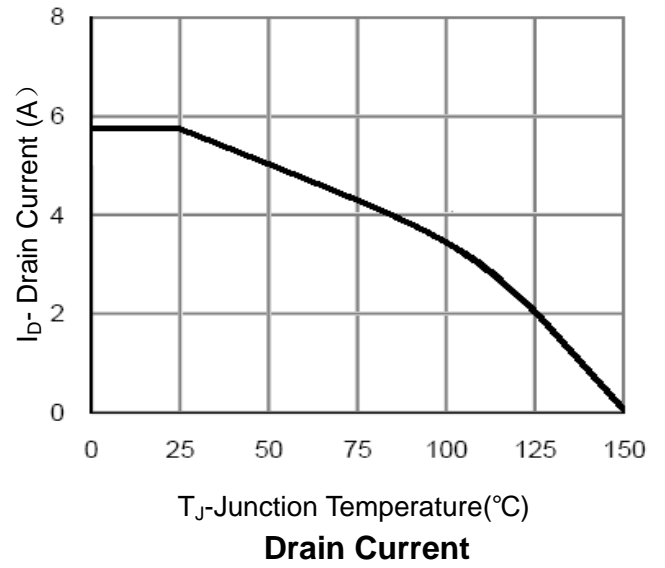
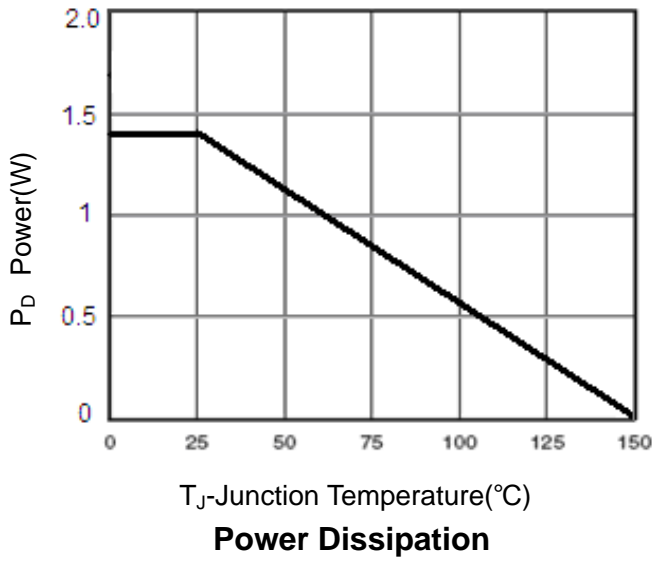
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	0.9	1.4	V
Drain-Source On-State Resistance ^{Note3}	R _{DS(ON)}	V _{GS} =2.5V, I _D =4A	-	-	45	mΩ
		V _{GS} =4.5V, I _D =5A	-	-	31	mΩ
		V _{GS} =10V, I _D =5.8A	-	-	27	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =5V, I _D =5A	10	-	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1.0MHz	-	825	-	pF
Output Capacitance	C _{oss}		-	100	-	pF
Reverse Transfer Capacitance	C _{rss}		-	78	-	pF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =2.7Ω V _{GS} =10V, R _{GEN} =3Ω	-	3.3	-	nS
Turn-on Rise Time	t _r		-	4.8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =5.8A, V _{GS} =4.5V	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	1.6	-	nC
Gate-Drain Charge	Q _{gd}		-	3.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V, I _S =5.8A	-	-	1.2	V
Diode Forward Current ^{Note2}	I _S		-	-	5.8	A

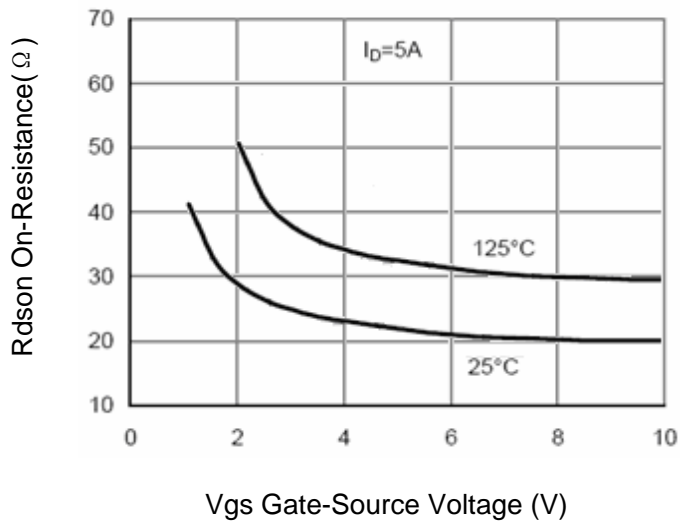
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.

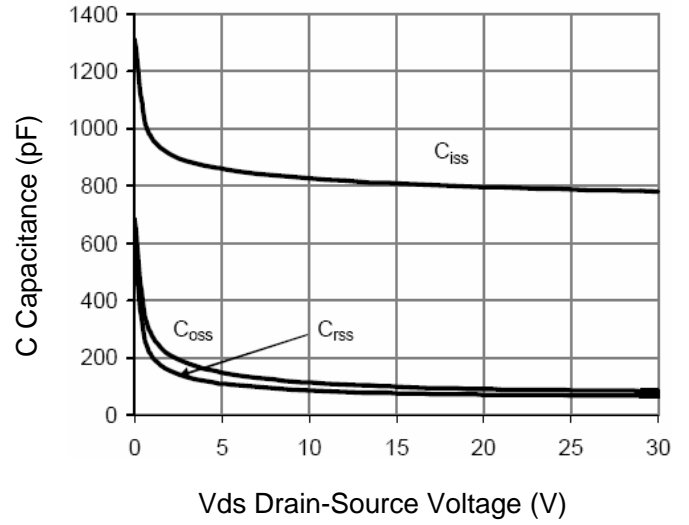


Typical Characteristics Curves

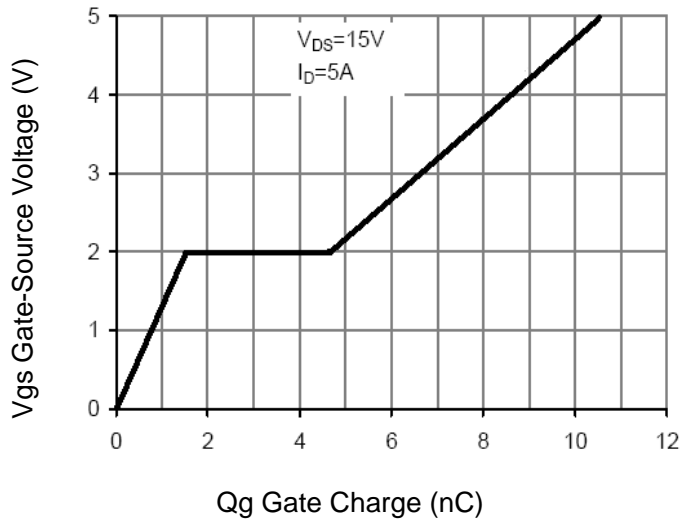




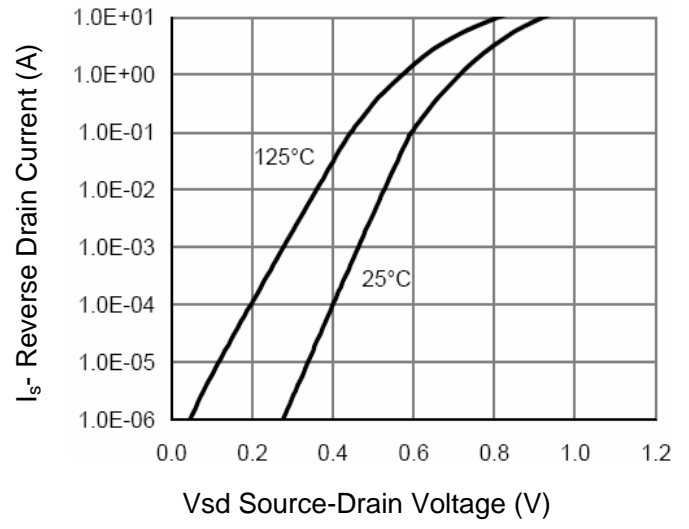
Rdson vs Vgs



Capacitance vs Vds



Gate Charge



Source- Drain Diode Forward



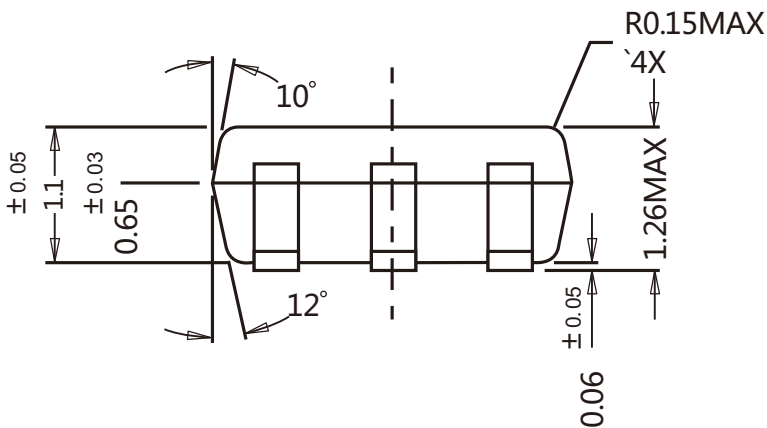
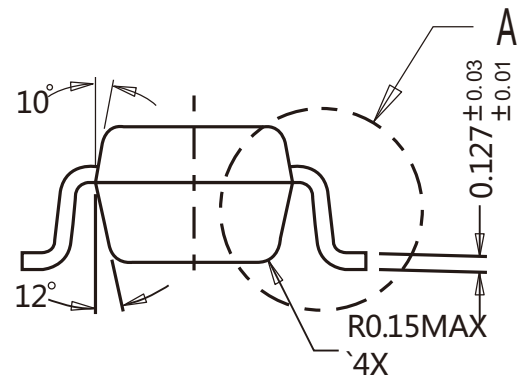
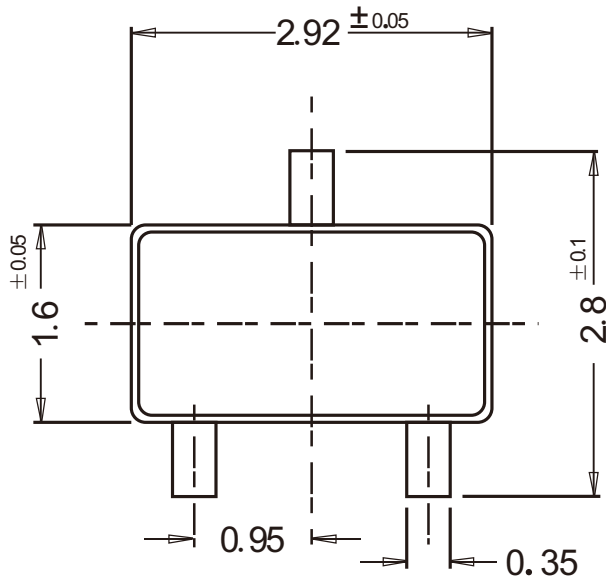
PJM3400NSC

N- Enhancement Mode Field Effect Transistor

Package Outline

SOT-23-3

Dimensions in mm



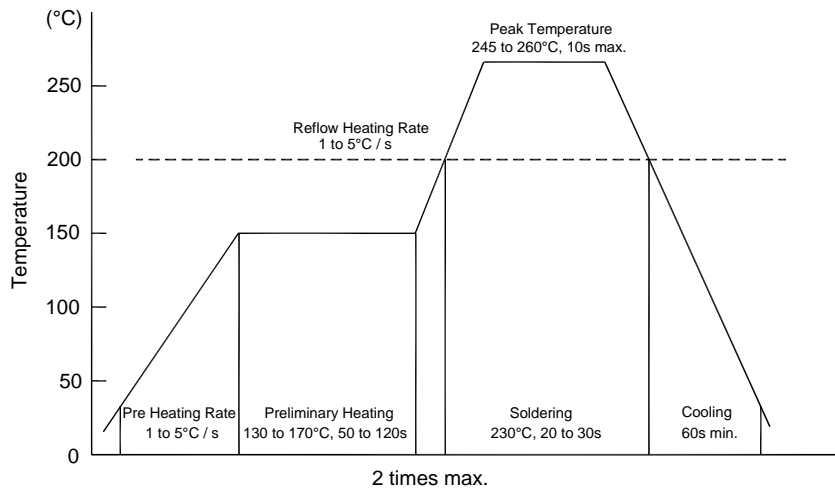
Ordering Information

Device	Package	Shipping
PJM3400NSC	SOT-23-3	3000/Reel&Tape(7inch)



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

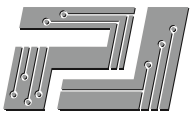
- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing



PJM3400NSC

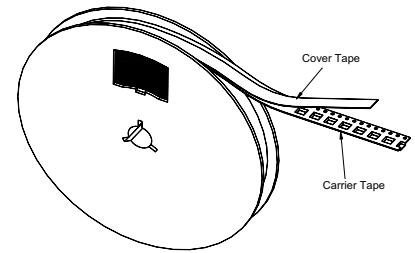
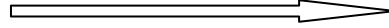
N- Enhancement Mode Field Effect Transistor

Package Specifications

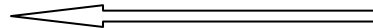
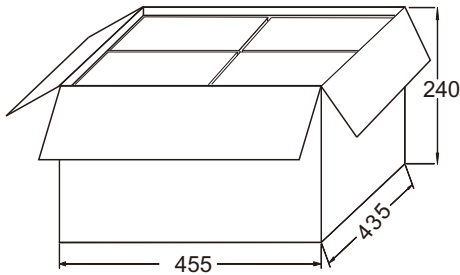
SOT-23-3



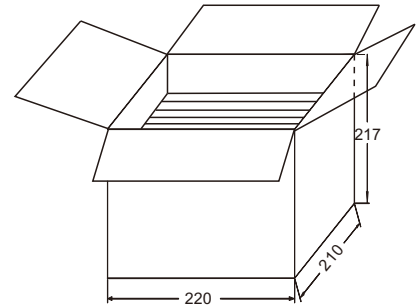
3,000 pcs per reel



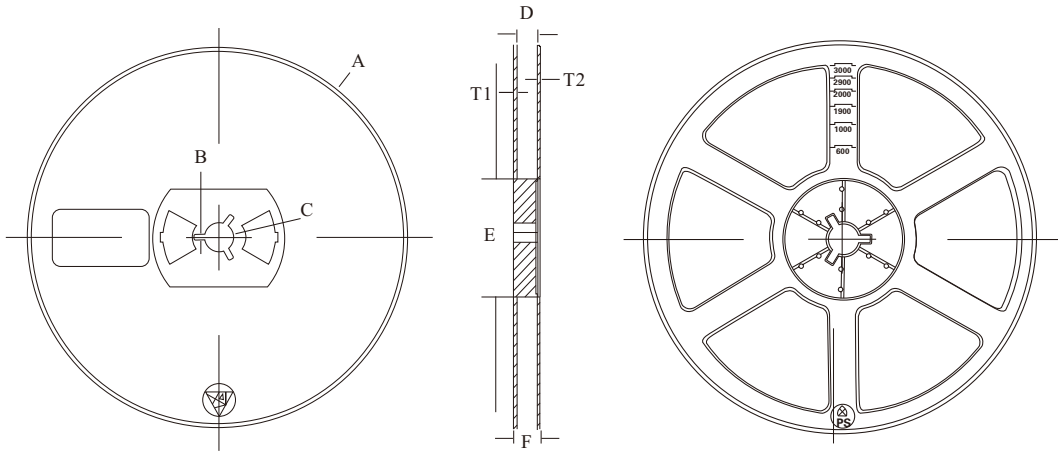
30,000 pcs per box
10 reels per box



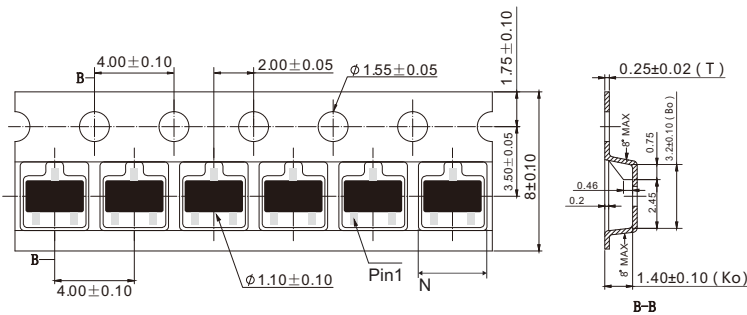
120,000 pcs per carton
4 boxes per carton



2. Tape and reel data(7inch Units:mm)



Reel (7")



Tape (8mm)

Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2
N	3.15±0.1
G	1.22±0.1

单击下面可查看定价，库存，交付和生命周期等信息

[>>PJSEMI\(平晶微\)](#)